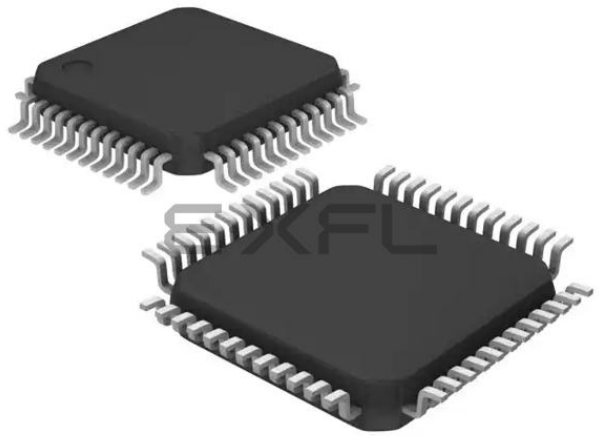

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	EBI/EMI, I²C, SPI, UART/USART, USB OTG
Peripherals	DMA, I²S, LVD, POR, PWM
Number of I/O	35
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 11x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/pcf51jf64vlf

Table 1. Voltage and current operating requirements (continued)

Symbol	Description	Min.	Max.	Unit	Notes
	• $2.7\ V \le V_{DD} \le 3.6\ V$ • $1.7\ V \le V_{DD} \le 2.7\ V$				
V_{IL}	Input low voltage • $2.7\ V \le V_{DD} \le 3.6\ V$ • $1.7\ V \le V_{DD} \le 2.7\ V$	— —	$0.35 \times V_{DD}$ $0.3 \times V_{DD}$	V V	2
I_{IC}	DC injection current — single pin • $V_{IN} > V_{DD}$ • $V_{IN} < V_{SS}$	0 0	2 –0.2	mA mA	3
	DC injection current — total MCU limit, includes sum of all stressed pins • $V_{IN} > V_{DD}$ • $V_{IN} < V_{SS}$	0 0	25 –5	mA mA	3
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	

1. The device always interprets an input as a 1 when the input is greater than or equal to V_{IH} (min.) and less than or equal to V_{IH} (max.), regardless of whether input hysteresis is turned on.
2. The device always interprets an input as a 0 when the input is less than or equal to V_{IL} (max.) and greater than or equal to V_{IL} (min.), regardless of whether input hysteresis is turned on.
3. All functional non-supply pins are internally clamped to VSS and VDD. Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the larger of the two values. Power supply must maintain regulation within operating VDD range during instantaneous and operating maximum current conditions. If positive injection current (VIn > VDD) is greater than IDD, the injection current may flow out of VDD and could result in external power supply going out of regulation. Ensure external VDD load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if clock rate is very low (which would reduce overall power consumption).

5.2.2 LVD and POR operating requirements

Table 2. LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
V_{LVW1H} V_{LVW2H} V_{LVW3H} V_{LVW4H}	Low-voltage warning thresholds — high range • Level 1 falling (LVWV=00) • Level 2 falling (LVWV=01) • Level 3 falling (LVWV=10) • Level 4 falling (LVWV=11)	2.62 2.72 2.82 2.92	2.70 2.80 2.90 3.00	2.78 2.88 2.98 3.08	V V V V	1
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	

Table continues on the next page...

Table 2. LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
V_{LVW1L} V_{LVW2L} V_{LVW3L} V_{LVW4L}	Low-voltage warning thresholds — low range • Level 1 falling (LVWV=00) • Level 2 falling (LVWV=01) • Level 3 falling (LVWV=10) • Level 4 falling (LVWV=11)	1.74 1.84 1.94 2.04	1.80 1.90 2.00 2.10	1.86 1.96 2.06 2.16	V V V V	1
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t_{LPO}	Internal low power oscillator period factory trimmed	900	1000	1100	µs	

1. Rising thresholds are falling threshold + hysteresis voltage

5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = - 9 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -3 mA	V_{DD} – 0.5	—	V	
	Output high voltage — low drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -2 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -0.6 mA	V_{DD} – 0.5	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — high drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 9 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 3 mA	—	0.5	V	
	Output low voltage — low drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 2 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 0.6 mA	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin)				
	• @ full temperature range	—	1.0	µA	1
	• @ 25 °C	—	0.1	µA	

Table continues on the next page...

Table 3. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Max.	Unit	Notes
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
I_{OZ}	Total Hi-Z (off-state) leakage current (all input pins)	—	4	μA	
R_{PU}	Internal pullup resistors	22	50	kΩ	2
R_{PD}	Internal pulldown resistors	22	50	kΩ	3

1. Tested by ganged leakage method
2. Measured at Vinput = V_{SS}
3. Measured at Vinput = V_{DD}

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx-RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 50 MHz
- Bus clock (and flash and Mini-FlexBus clocks) = 25 MHz

Table 4. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip. • 1.71 V/(V_{DD} slew rate) ≤ 300 μs • 1.71 V/(V_{DD} slew rate) > 300 μs	—	300 1.71 V/(V_{DD} slew rate)	μs	1
	• VLLS1 → RUN	—	132	μs	1, 2
	• VLLS2 → RUN	—	92	μs	1, 2
	• VLLS3 → RUN	—	92	μs	1, 2
	• LLS → RUN	—	7.5	μs	2
	• VLPS → RUN	—	5.5	μs	2
	• STOP → RUN	—	5.5	μs	2

1. Normal boot (FTFL_FOPT[LPBOOT] is 1)
2. The wakeup time includes the execution time for a small amount of firmware used to produce a GPIO clear event. Wakeup time is measured from the falling edge of the external wakeup event to the falling edge of a GPIO clear performed by software.

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• @ –40 to 25 °C • @ 105 °C					
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V • @ –40 to 25 °C • @ 105 °C	— —	1.4 17.6	2.6 50	µA µA	8,9
I_{DD_RTC}	Average current adder for real-time clock function • @ –40 to 25 °C	—	0.7	—	µA	11

1. The analog supply current is the sum of the active current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50 MHz core and system clocks, and 25 MHz bus clock. MCG configured for FEI mode. All peripheral clocks disabled.
3. 50 MHz core and system clocks, and 25 MHz bus clock. MCG configured for FEI mode. All peripheral clocks enabled, but peripherals are not in active operation.
4. 50 MHz core and system clocks, and 25 MHz bus clock. MCG configured for FEI mode.
5. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks disabled. Code executing from flash memory.
6. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks enabled, but peripherals are not in active operation. Code executing from flash memory.
7. 2 MHz core and system clocks, and 1 MHz bus clock. MCG configured for BLPE mode. All peripheral clocks disabled.
8. OSC clocks disabled.
9. All pads disabled.
10. Data reflects devices with 32 KB of RAM. For devices with 16 KB of RAM, power consumption is reduced by 500 nA. For devices with 8 KB of RAM, power consumption is reduced by 750 nA.
11. RTC function current includes LPTMR with OSC enabled with 32.768 kHz crystal at 3.0 V

5.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE mode, except for 50 MHz core (FEI mode)
- For the ALLOFF curve, all peripheral clocks are disabled except FTFL
- For the ALLON curve, all peripheral clocks are enabled, but peripherals are not in active operation
- USB Voltage Regulator disabled
- No GPIOs toggled
- Code execution from flash memory with cache enabled

Table 13. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70°C		—	± 4.5	—	$\%f_{dco}$	1
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal VDD and 25°C		—	3.3	4	MHz	
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal VDD and 25 °C		3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00		(3/5) x f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11		(16/5) x f_{ints_t}	—	—	kHz	
FLL							
f_{fll_ref}	FLL reference frequency range		31.25	—	39.0625	kHz	
f_{dco}	DCO output frequency range	Low range (DRS=00) 640 × f_{fll_ref}	20	20.97	25	MHz	2, 3
		Mid range (DRS=01) 1280 × f_{fll_ref}	40	41.94	50	MHz	
		Mid-high range (DRS=10) 1920 × f_{fll_ref}	60	62.91	75	MHz	
		High range (DRS=11) 2560 × f_{fll_ref}	80	83.89	100	MHz	
$f_{dco\_t\_DMX32}$	DCO output frequency	Low range (DRS=00) 732 × f_{fll_ref}	—	23.99	—	MHz	4, 5
		Mid range (DRS=01) 1464 × f_{fll_ref}	—	47.97	—	MHz	
		Mid-high range (DRS=10) 2197 × f_{fll_ref}	—	71.99	—	MHz	
		High range (DRS=11) 2929 × f_{fll_ref}	—	95.98	—	MHz	
J_{cyc_fll}	FLL period jitter • f_{DCO} = 48 MHz • f_{DCO} = 98 MHz		— —	180 150	— —	ps	
$t_{fll\_acquire}$	FLL target frequency acquisition time		—	—	1	ms	6
PLL							
f_{vco}	VCO operating frequency		48.0	—	100	MHz	
I_{pll}	PLL operating current • PLL @ 96 MHz ($f_{osc\_hi\_1}$ = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 48)		—	1060	—	µA	7
I_{pll}	PLL operating current • PLL @ 48 MHz ($f_{osc\_hi\_1}$ = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 24)		—	600	—	µA	7
f_{pll_ref}	PLL reference frequency range		2.0	—	4.0	MHz	

Table continues on the next page...

Table 14. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• 16 MHz	—	1.2	—	mA	
	• 24 MHz	—	1.5	—	mA	
	• 32 MHz					
I_{DDOSC}	Supply current — high-gain mode (HGO=1)					1
	• 32 kHz	—	25	—	µA	
	• 1 MHz	—	300	—	µA	
	• 4 MHz	—	400	—	µA	
	• 8 MHz (RANGE=01)	—	500	—	µA	
	• 16 MHz	—	2.5	—	mA	
	• 24 MHz	—	3	—	mA	
	• 32 MHz	—	4	—	mA	
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)					
	• 1 MHz resonator	—	6.6	—	kΩ	
	• 2 MHz resonator	—	3.3	—	kΩ	
	• 4 MHz resonator	—	0	—	kΩ	
	• 8 MHz resonator	—	0	—	kΩ	
	• 16 MHz resonator	—	0	—	kΩ	
	• 20 MHz resonator	—	0	—	kΩ	
	• 32 MHz resonator	—	0	—	kΩ	
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	

Table continues on the next page...

6.4 Memories and memory interfaces

6.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 16. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	µs	—
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk32k}$	Erase Block high-voltage time for 32 KB	—	52	452	ms	1
$t_{hversblk128k}$	Erase Block high-voltage time for 128 KB	—	208	1808	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 17. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Read 1s Block execution time					1
$t_{rd1blk32k}$	• 32 KB data flash	—	—	0.5	ms	
$t_{rd1blk128k}$	• 128 KB program flash	—	—	1.7	ms	
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	µs	1
t_{pgmchk}	Program Check execution time	—	—	45	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	µs	1
t_{pgm4}	Program Longword execution time	—	65	145	µs	—
	Erase Flash Block execution time					2
$t_{ersblk32k}$	• 32 KB data flash	—	55	465	ms	
$t_{ersblk128k}$	• 128 KB program flash	—	220	1850	ms	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
	Program Section execution time					—
$t_{pgmsec512}$	• 512 bytes flash	—	4.7	—	ms	
$t_{pgmsec1k}$	• 1 KB flash	—	9.3	—	ms	

Table continues on the next page...

Table 17. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	1
t_{rdonce}	Read Once execution time	—	—	25	µs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	µs	—
t_{ersall}	Erase All Blocks execution time	—	275	2350	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1
	Program Partition for EEPROM execution time					—
$t_{pgmpart32k}$	• 32 KB FlexNVM	—	70	—	ms	
	Set FlexRAM Function execution time:					—
$t_{setramff}$	• Control Code 0xFF	—	50	—	µs	
$t_{setram8k}$	• 8 KB EEPROM backup	—	0.3	0.5	ms	
$t_{setram32k}$	• 32 KB EEPROM backup	—	0.7	1.0	ms	
	Byte-write to FlexRAM for EEPROM operation					
$t_{eewr8bers}$	Byte-write to erased FlexRAM location execution time	—	175	260	µs	3
	Byte-write to FlexRAM execution time:					—
$t_{eewr8b8k}$	• 8 KB EEPROM backup	—	340	1700	µs	
$t_{eewr8b16k}$	• 16 KB EEPROM backup	—	385	1800	µs	
$t_{eewr8b32k}$	• 32 KB EEPROM backup	—	475	2000	µs	
	Word-write to FlexRAM for EEPROM operation					
$t_{eewr16bers}$	Word-write to erased FlexRAM location execution time	—	175	260	µs	—
	Word-write to FlexRAM execution time:					—
$t_{eewr16b8k}$	• 8 KB EEPROM backup	—	340	1700	µs	
$t_{eewr16b16k}$	• 16 KB EEPROM backup	—	385	1800	µs	
$t_{eewr16b32k}$	• 32 KB EEPROM backup	—	475	2000	µs	
	Longword-write to FlexRAM for EEPROM operation					
$t_{eewr32bers}$	Longword-write to erased FlexRAM location execution time	—	360	540	µs	—
	Longword-write to FlexRAM execution time:					—
$t_{eewr32b8k}$	• 8 KB EEPROM backup	—	545	1950	µs	
$t_{eewr32b16k}$	• 16 KB EEPROM backup	—	630	2050	µs	
$t_{eewr32b32k}$	• 32 KB EEPROM backup	—	810	2250	µs	

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

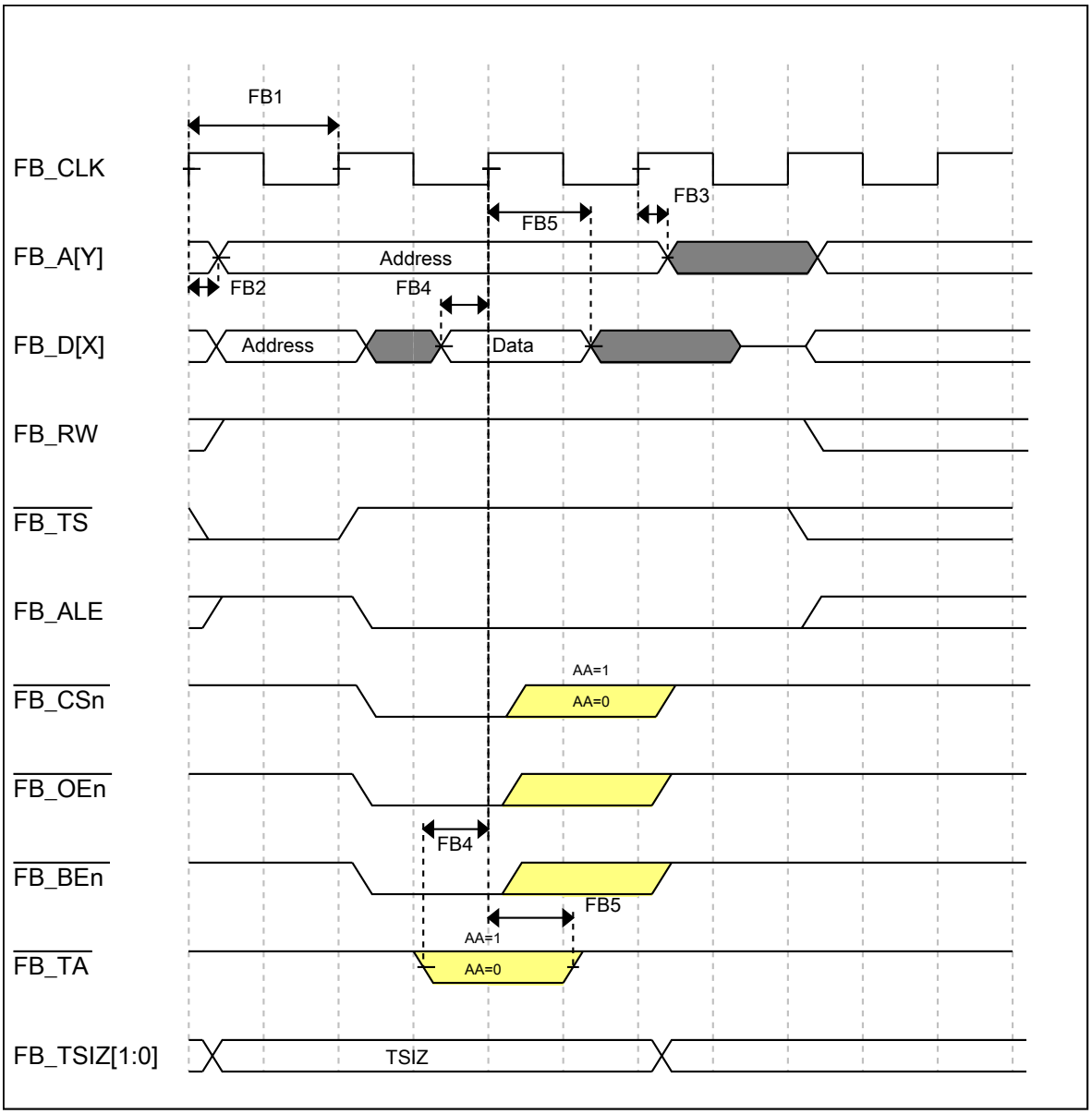


Figure 6. Mini-FlexBus read timing diagram

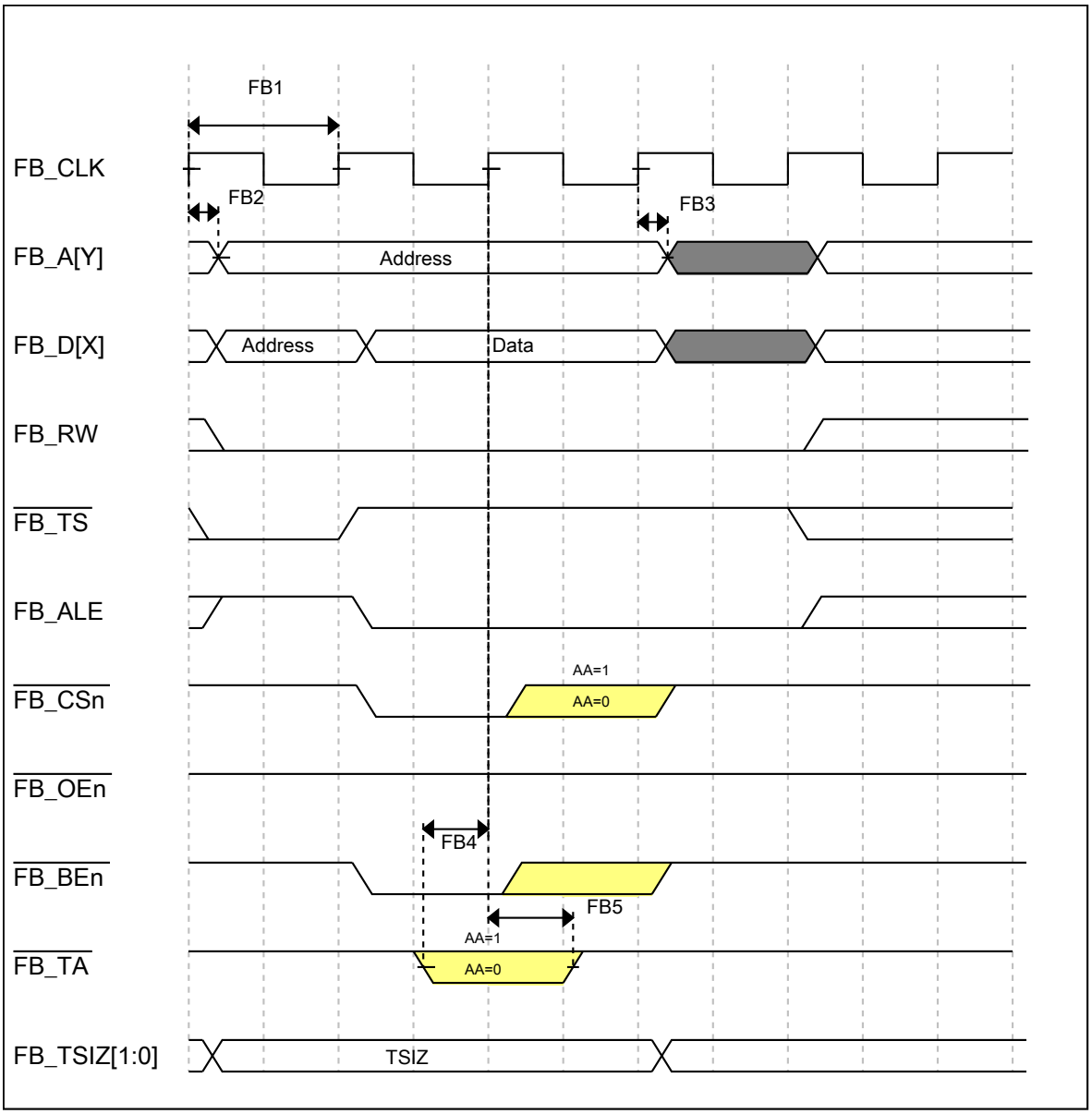


Figure 7. Mini-FlexBus write timing diagram

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

Table 23. 12-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	–4 –1.4	–5.4 –1.8	LSB[4]	$V_{ADIN} = V_{DDA}$[5]
E_Q	Quantization error	• 12-bit modes	—	—	±0.5	LSB[4]	
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	–40°C to 25°C 25 to 105°C		1.695 1.713		mV/°C	6
V_{TEMP25}	Temp sensor voltage	25 °C		716		mV	6

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. ADC conversion clock < 3 MHz

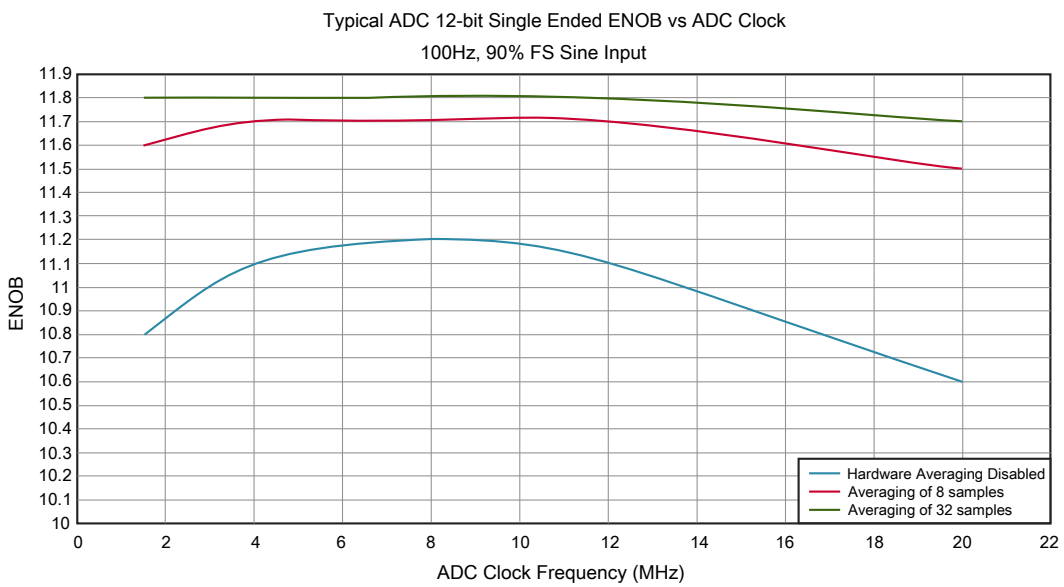


Figure 9. Typical ENOB vs. ADC_CLK for 12-bit single-ended mode

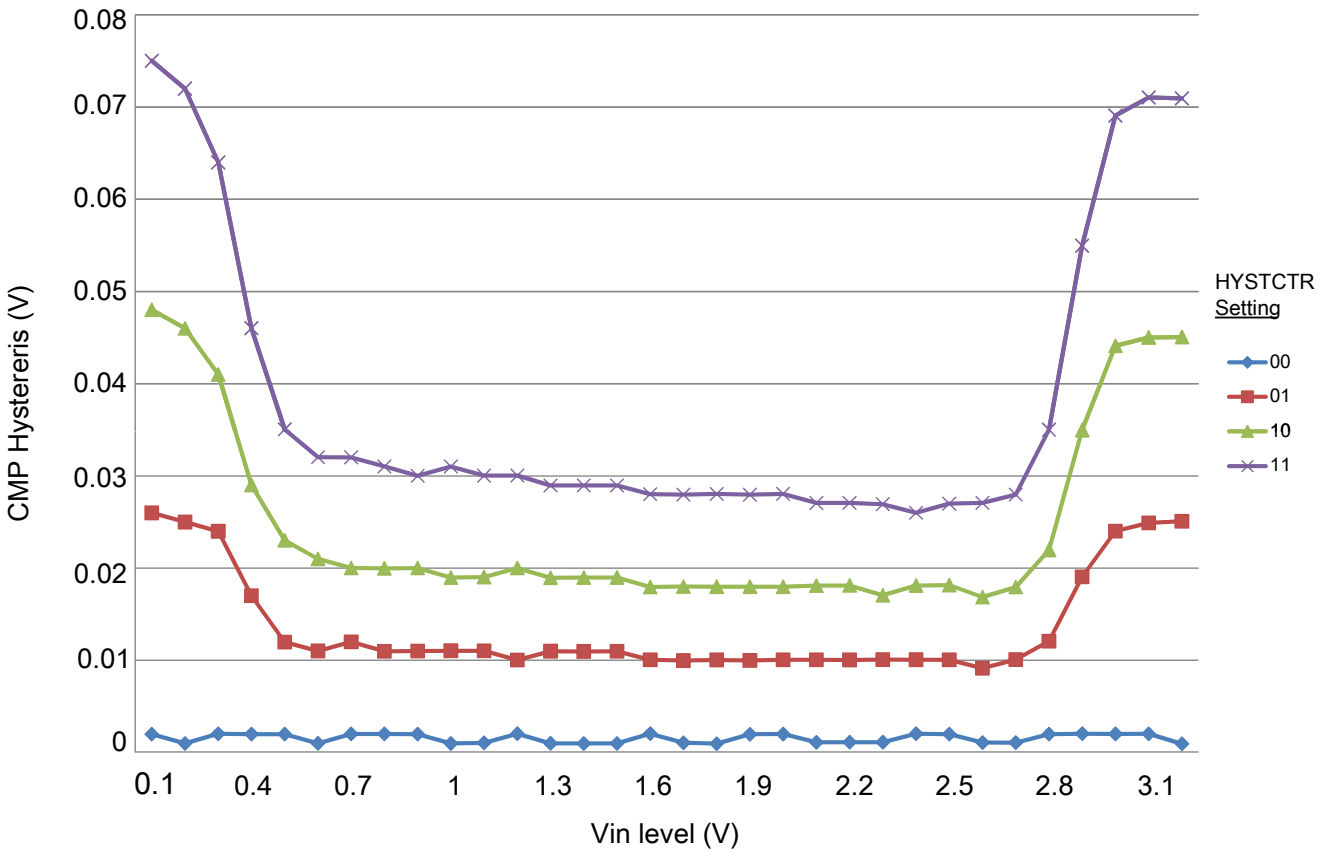


Figure 10. Typical hysteresis vs. Vin level (VDD = 3.3 V, PMODE = 0)

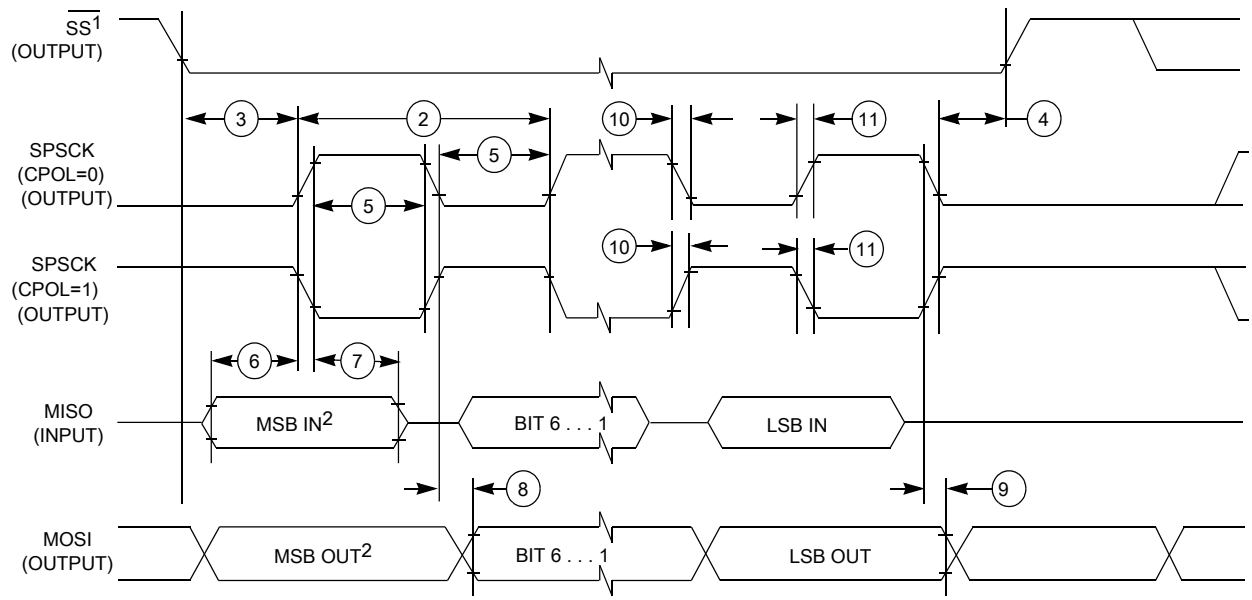
6.8.4 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 70% V_{DD}, unless noted, as well as input signal transitions of 3 ns and a 50 pF maximum load on all SPI pins. All timing assumes slew rate control is disabled and high drive strength is enabled for SPI output pins.

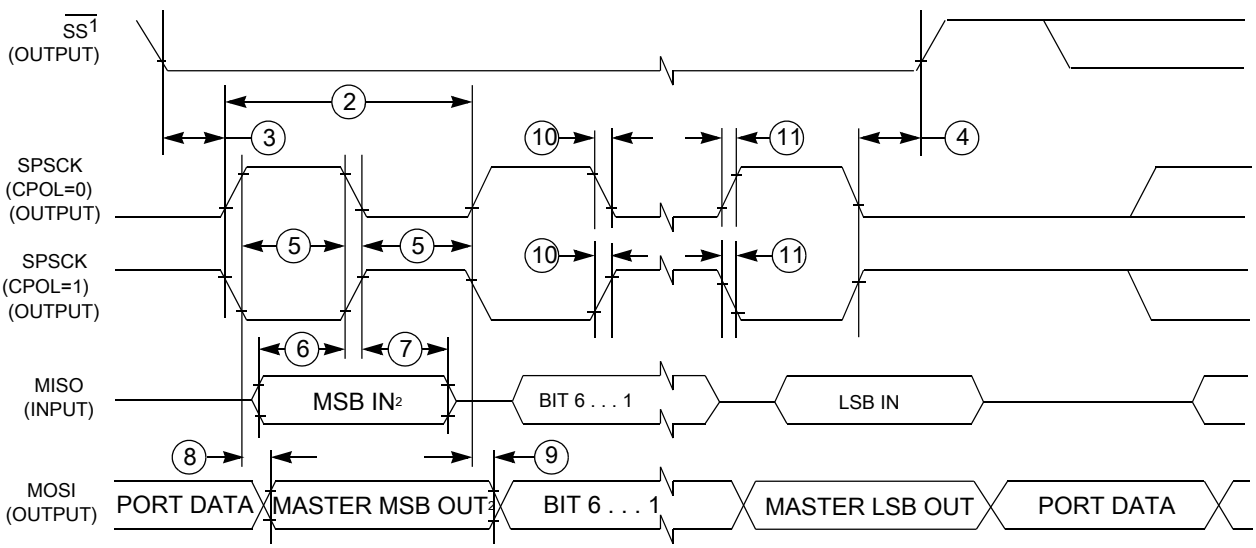
Table 33. SPI master mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	$f_{BUS}/2048$	$f_{BUS}/2$	Hz	f_{BUS} is the bus clock as defined in Table 8.
2	t_{SPSCK}	SPSCK period	2 x t_{BUS}	2048 x t_{BUS}	ns	t_{BUS} = 1/ f_{BUS}
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{BUS} - 30	1024 x t_{BUS}	ns	—
6	t_{SU}	Data setup time (inputs)	21	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_{v}	Data valid (after SPSCK edge)	—	25	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	t_{BUS} - 25	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 14. SPI master mode timing (CPHA=0)



1.If configured as output
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 15. SPI master mode timing (CPHA=1)

Table 34. SPI slave mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	0	$f_{BUS}/4$	Hz	f_{BUS} is the bus clock as defined in Table 8.
2	t_{SPSCK}	SPSCK period	4 x t_{BUS}	—	ns	t_{BUS} = 1/ f_{BUS}

Table continues on the next page...

Table 38. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
61	45	41		PTF7	PTF7
5 V VREG					
20	16	14	11		VOUT33
19	15	13	10		VREGIN
USB0					
63	47	43	31	PTC4	USB_SOF_PULSE
62	46	42	30	PTC3	USB_CLKIN
21	17	15	12		USB0_DM
22	18	16	13		USB0_DP
20	16	14	11		VOUT33
19	15	13	10		VREGIN
ADC0					
11	7	5	5	PTA4	ADC0_SE2
12	8	6	6	PTA5	ADC0_SE3
25	21	19	15	PTA6	ADC0_SE8
26				PTD2	ADC0_SE9
27	22	20		PTD3	ADC0_SE10
28				PTD4	ADC0_SE11
29				PTD5	ADC0_SE12
30	23	21	16	PTA7	ADC0_SE13
31	24	22		PTD6	ADC0_SE14
32				PTD7	ADC0_SE15
38				PTE3	ADC0_SE16
39	27	25	19	PTB2	ADC0_SE17
40	28	26	20	PTB3	ADC0_SE18
41	29			PTE4	ADC0_SE19
42	30			PTE5	ADC0_SE20
43				PTE6	ADC0_SE21
44	31	27		PTE7	ADC0_SE22
13	9	7	7		VDDA
14	10	8			VREFH
16	12	10			VREFL
17	13	11	8		VSSA
DAC0					
18	14	12	9		DAC0_OUT
VREF					
15	11	9			VREF_OUT
CMP0					
53				PTF0	CMP0_IN0

Table continues on the next page...

Table 38. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
55				PTF2	CMP0_IN1
56	40	36		PTF3	CMP0_IN2
57	41	37	29	PTC2	CMP0_IN3
54				PTF1	CMP0_OUT
CMT					
64	48	44	32	PTC5	CMT_IRO
I2S0					
5	1			PTD0	I2S0_MCLK/ I2S0_CLKIN
62	46	42	30	PTC3	I2S0_MCLK/ I2S0_CLKIN
6	2			PTD1	I2S0_RX_BCLK
61	45	41		PTF7	I2S0_RX_BCLK
7	3	1	1	PTA0	I2S0_RX_FS
60	44	40		PTF6	I2S0_RX_FS
8	4	2	2	PTA1	I2S0_RXD
59	43	39		PTF5	I2S0_RXD
10	6	4	4	PTA3	I2S0_TX_BCLK
58	42	38		PTF4	I2S0_TX_BCLK
11	7	5	5	PTA4	I2S0_TX_FS
57	41	37	29	PTC2	I2S0_TX_FS
12	8	6	6	PTA5	I2S0_TXD
56	40	36		PTF3	I2S0_TXD
TSI0					
25	21	19	15	PTA6	TSI0_CH0
26				PTD2	TSI0_CH1
27	22	20		PTD3	TSI0_CH2
28				PTD4	TSI0_CH3
29				PTD5	TSI0_CH4
30	23	21	16	PTA7	TSI0_CH5
31	24	22		PTD6	TSI0_CH6
32				PTD7	TSI0_CH7
33				PTE0	TSI0_CH8
34				PTE1	TSI0_CH9
36	26	24	18	PTB1	TSI0_CH10
37				PTE2	TSI0_CH11
38				PTE3	TSI0_CH12
39	27	25	19	PTB2	TSI0_CH13
40	28	26	20	PTB3	TSI0_CH14
41	29			PTE4	TSI0_CH15

Table continues on the next page...

Table 38. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
56	40	36		PTF3	FBa_AD8
60	44	40		PTF6	FBa_AD9
61	45	41		PTF7	FBa_AD10
3				PTC6	FBa_AD11
4				PTC7	FBa_AD12
5	1			PTD0	FBa_AD13
6	2			PTD1	FBa_AD14
7	3	1	1	PTA0	FBa_AD15
8	4	2	2	PTA1	FBa_AD16
25	21	19	15	PTA6	FBa_AD17
57	41	37	29	PTC2	FBa_AD18
58	42	38		PTF4	FBa_AD19
40	28	26	20	PTB3	FBa_ALE
39	27	25	19	PTB2	FBa_CS0_b
37				PTE2	FBa_D0
34				PTE1	FBa_D1
33				PTE0	FBa_D2
32				PTD7	FBa_D3
31	24	22		PTD6	FBa_D4
30	23	21	16	PTA7	FBa_D5
29				PTD5	FBa_D6
28				PTD4	FBa_D7
38				PTE3	FBa_OE_b
59	43	39		PTF5	FBa_RW_b
DATA_BUS					
8	4	2	2	PTA1	FBa_AD16
39	27	25	19	PTB2	FBa_CS0_b
61	45	41		PTF7	FBa_D0
60	44	40		PTF6	FBa_D1
59	43	39		PTF5	FBa_D2
58	42	38		PTF4	FBa_D3
31	24	22		PTD6	FBa_D4
30	23	21	16	PTA7	FBa_D5
27	22	20		PTD3	FBa_D6
25	21	19	15	PTA6	FBa_D7
44	31	27		PTE7	FBa_RW_b
I2C0 and I2C1					
3				PTC6	I2C0_SCL
35	25	23	17	PTB0	I2C0_SCL

Table continues on the next page...

Table 38. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
4				PTC7	I2C0_SDA
36	26	24	18	PTB1	I2C0_SDA
6	2			PTD1	I2C1_SCL
42	30			PTE5	I2C1_SCL
51	38	34	27	PTC0	I2C1_SCL
5	1			PTD0	I2C1_SDA
43				PTE6	I2C1_SDA
50	37	33	26	PTB7	I2C1_SDA
I2C2 and I2C3					
7	3	1	1	PTA0	I2C2_SCL
11	7	5	5	PTA4	I2C2_SCL
8	4	2	2	PTA1	I2C2_SDA
12	8	6	6	PTA5	I2C2_SDA
32				PTD7	I2C3_SCL
37				PTE2	I2C3_SCL
33				PTE0	I2C3_SDA
38				PTE3	I2C3_SDA
SPI0					
39	27	25	19	PTB2	SPI0_MISO
55				PTF2	SPI0_MISO
63	47	43	31	PTC4	SPI0_MISO
38				PTE3	SPI0_MOSI
40	28	26	20	PTB3	SPI0_MOSI
56	40	36		PTF3	SPI0_MOSI
64	48	44	32	PTC5	SPI0_MOSI
36	26	24	18	PTB1	SPI0_SCLK
54				PTF1	SPI0_SCLK
62	46	42	30	PTC3	SPI0_SCLK
7	3	1	1	PTA0	SPI0_SS
34				PTE1	SPI0_SS
53				PTF0	SPI0_SS
61	45	41		PTF7	SPI0_SS
SPI1					
4				PTC7	SPI1_MISO
11	7	5	5	PTA4	SPI1_MISO
43				PTE6	SPI1_MISO
59	43	39		PTF5	SPI1_MISO
3				PTC6	SPI1_MOSI
12	8	6	6	PTA5	SPI1_MOSI

Table continues on the next page...

Table 38. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
44	31	27		PTE7	SPI1_MOSI
60	44	40		PTF6	SPI1_MOSI
5	1			PTD0	SPI1_SCLK
10	6	4	4	PTA3	SPI1_SCLK
42	30			PTE5	SPI1_SCLK
58	42	38		PTF4	SPI1_SCLK
6	2			PTD1	SPI1_SS
9	5	3	3	PTA2	SPI1_SS
41	29			PTE4	SPI1_SS
57	41	37	29	PTC2	SPI1_SS
UART0					
5	1			PTD0	UART0_CTS_b
32				PTD7	UART0_CTS_b
42	30			PTE5	UART0_CTS_b
62	46	42	30	PTC3	UART0_CTS_b
6	2			PTD1	UART0_RTS_b
33				PTE0	UART0_RTS_b
41	29			PTE4	UART0_RTS_b
61	45	41		PTF7	UART0_RTS_b
4				PTC7	UART0_RX
31	24	22		PTD6	UART0_RX
43				PTE6	UART0_RX
63	47	43	31	PTC4	UART0_RX
3				PTC6	UART0_TX
30	23	21	16	PTA7	UART0_TX
44	31	27		PTE7	UART0_TX
64	48	44	32	PTC5	UART0_TX
UART1					
11	7	5	5	PTA4	UART1_CTS_b
58	42	38		PTF4	UART1_CTS_b
12	8	6	6	PTA5	UART1_RTS_b
57	41	37	29	PTC2	UART1_RTS_b
10	6	4	4	PTA3	UART1_RX
59	43	39		PTF5	UART1_RX
9	5	3	3	PTA2	UART1_TX
60	44	40		PTF6	UART1_TX

9 Revision History

The following table summarizes content changes since the previous release of this document.

Table 39. Revision History

Rev. No.	Date	Substantial Changes
7	03/2015	• Updated the value and description in Power mode transition operating behaviors • Updated the maximum value of f_{fll_ref} in MCG specs • 12-bit ADC characteristics: Updated the values of temperature sensor slope for -40°C to 25°C and 25°C to 105°C • Updated the minimum and typical values of V_{out} in VREF full-range operating behaviors • Updated the maximum internal reference frequency and maximum FLL reference frequency range in MCG specifications • Updated the values of Temperature sensor voltage in 12-bit ADC characteristics • Removed the temperature parameter from VREF full-range operating requirements table • Removed Write endurance to FlexRAM for EEPROM section • Removed ADC calculator tool footnote from ADC operating conditions